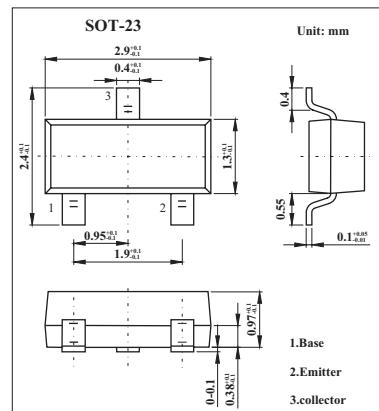


Silicon PNP Epitaxial Planar Type

2SC2404

■ Features

- Optimum for RF amplification of FM/AM radios
- High transition frequency fT
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{C EO}	20	V
Emitter-base voltage	V _{EBO}	3	V
Collector current	I _C	15	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V _{CBO}	I _C = 10 µA, I _E = 0	30			V
Emitter-base voltage	V _{EBO}	I _E = 10 µA, I _C = 0	3			V
Base-emitter voltage	V _{BE}	V _{CB} = 6 V, I _E = -1 mA		0.72		V
Forward current transfer ratio	h _{FE}	V _{CB} = 6 V, I _E = -1 mA	65		260	
Transition frequency	f _T	V _{CB} = 6 V, I _E = -1 mA, f = 100 MHz	450	650		MHz
Reverse transfer capacitance	C _{re}	V _{CB} = 6 V, I _E = -1 mA, f = 10.7 MHz		0.8	1.0	pF
Power gain	G _P	V _{CB} = 6 V, I _E = -1 mA, f = 100 MHz		24		dB
Noise figure	NF	V _{CB} = 6 V, I _E = -1 mA, f = 100 MHz		3.3		dB

■ h_{FE} Classification

Marking	U	
Rank	C	D
h _{FE}	65~160	100~260